

SOT223 PNP SILICON PLANAR
DARLINGTON TRANSISTORS

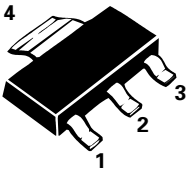
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FZTA63
FZTA64

PARTMARKING DETAILS: FULL DEVICE TYPE

COMPLIMENTARY TYPES: FZTA63 = FZTA13
FZTA64 = FZTA14



SOT223

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-10	V
Peak Pulse Current	I_{CM}	-800	mA
Continuous Collector Current	I_C	-500	mA
Peak Base Current	I_{BM}	-200	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER		SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	-30		V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	-30		V	$I_C = -10mA, I_B = 0^*$
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	-10		V	$I_E = -10\mu A, I_C = 0$
Collector Cut-Off Current		I_{CBO}		-100	nA	$V_{CB} = -30V, I_E = 0$
Emitter Cut-Off Current		I_{EBO}		-100	nA	$V_{EB} = -10V, I_C = 0$
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$		-1.5	V	$I_C = -100mA, I_B = -0.1mA^*$
Base-Emitter Saturation Voltage		$V_{BE(sat)}$		-2.0	V	$I_C = -100mA, I_B = -0.1mA^*$
Static Forward Current Transfer Ratio	FZTA63	h_{FE}	5K			$I_C = -10mA, V_{CE} = -5V$
	FZTA64		10K			$I_C = -100mA, V_{CE} = -5V^*$
			10K 20K			$I_C = -10mA, V_{CE} = -5V$ $I_C = -100mA, V_{CE} = -5V^*$
Transition Frequency		f_T	125		MHz	$I_C = -50mA, V_{CE} = -5V$ $f = 20MHz$

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%

FZTA63 FZTA64

TYPICAL CHARACTERISTICS

